

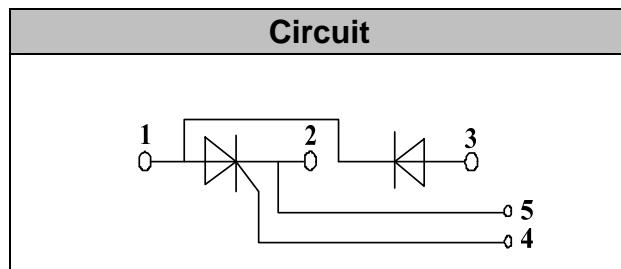


Thyristor/Diode Modules

V_{RRM} / V_{DRM} 800 to 1800V
I_{FAV} / I_{TAV} 40A

Applications

- Power Converters
- Lighting Control
- DC Motor Control and Drives
- Heat and temperature control



Features

- International standard package
- High Surge Capability
- Glass passivated chip
- Simple Mounting
- Heat transfer through aluminum oxide DBC ceramic isolated metal baseplate
- UL recognized applied for file no. E360040

Module Type

TYPE	V _{RRM/V_{DRM}}	V _{RSM}
MT40CB08T1	800V	900V
MT40CB12T1	1200V	1300V
MT40CB16T1	1600V	1700V
MT40CB18T1	1800V	1900V

◆Diode

Maximum Ratings

Symbol	Item	Conditions	Values	Units
I _D	Output Current(D.C.)	T _c =85°C	40	A
I _{FSM}	Surge forward current	t=10mS T _{vj} =45°C	1000	A
i ² t	Circuit Fusing Consideration		5000	A ² s
V _{Isol}	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
T _{vj}	Operating Junction Temperature		-40 to +125	°C
T _{stg}	Storage Temperature		-40 to +125	°C
M _t	Mounting Torque	To terminals(M5)	3±15%	Nm
M _s		To heatsink(M6)	5±15%	Nm
Weight	Module (Approximately)		100	g

Thermal Characteristics

Symbol	Item	Conditions	Values	Units
R _{th(j-c)}	Thermal Impedance, max.	Junction to Case	0.33	°C/W
R _{th(c-s)}	Thermal Impedance, max.	Case to Heatsink	0.10	°C/W

Electrical Characteristics

Symbol	Item	Conditions	Values			Units
			Min.	Typ.	Max.	
V _{FM}	Forward Voltage Drop, max.	T=25°C I _F =200A			1.95	V
I _{RRM}	Repetitive Peak Reverse Current, max.	T _{vj} =25°C V _{RD} =V _{RRM} T _{vj} =125°C V _{RD} =V _{RRM}		≤0.5 ≤6		mA mA

◆Thyristor

Maximum Ratings

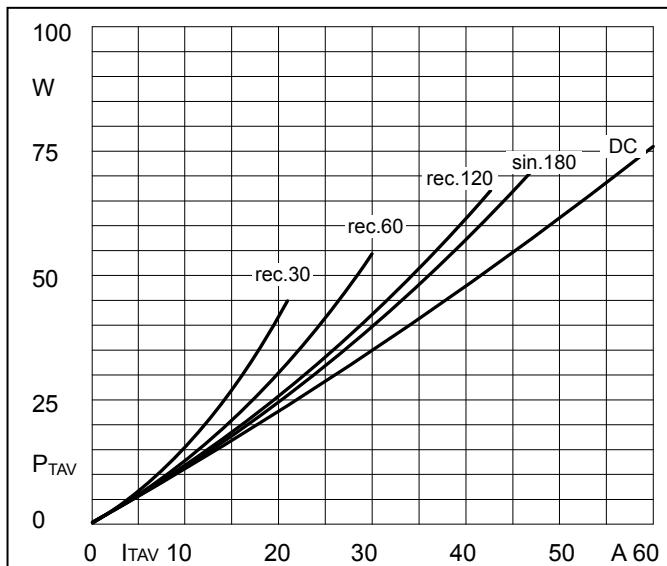
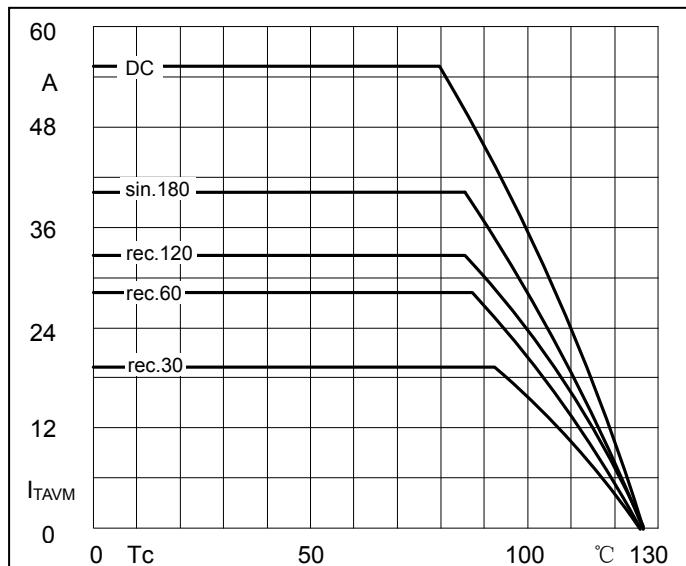
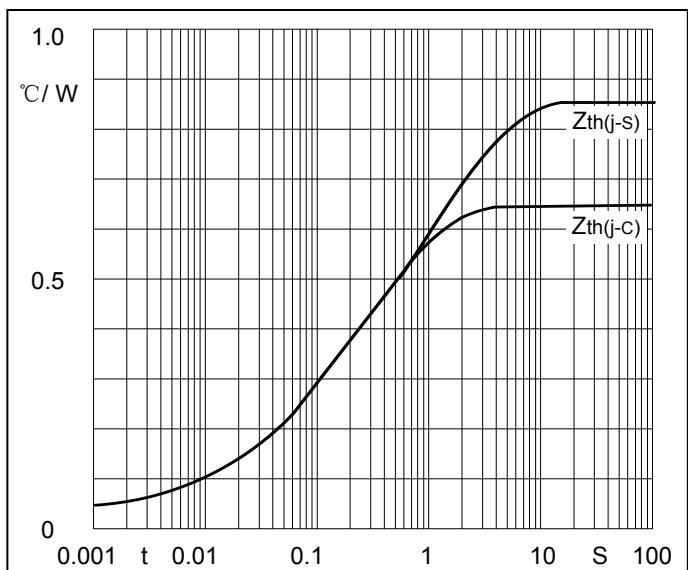
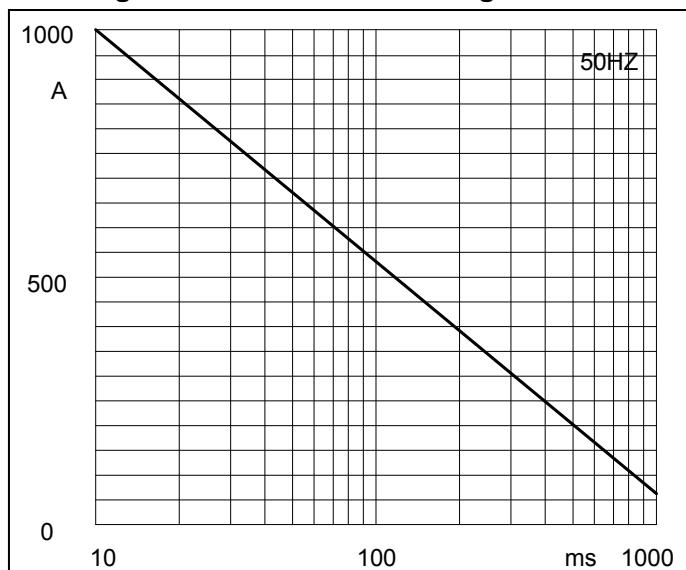
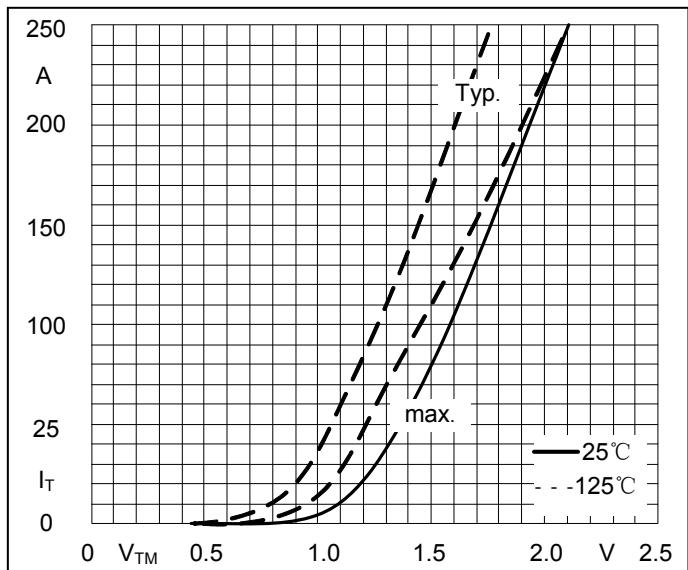
Symbol	Item	Conditions	Values	Units
I _{TAV}	Average On-State Current	Sine 180°; T _c =85°C	40	A
I _{TSM}	Surge On-State Current	T _{VJ} =45°C t=10ms, sine T _{VJ} =125°C t=10ms, sine	1000 850	A
i ² t	Circuit Fusing Consideration	T _{VJ} =45°C t=10ms, sine T _{VJ} =125°C t=10ms, sine	5000 3600	A ² s
Visol	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
T _{vj}	Operating Junction Temperature		-40 to +125	°C
T _{stg}	Storage Temperature		-40 to +125	°C
M _t	Mounting Torque	To terminals(M5)	3±15%	Nm
M _s		To heatsink(M6)	5±15%	Nm
di/dt	Critical Rate of Rise of On-State Current	T _{VJ} = T _{VJM} , 2/3V _{DRM} , I _G =500mA Tr<0.5us, tp>6us	150	A/us
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	T _J =T _{VJM} , 2/3V _{DRM} linear voltage rise	1000	V/us
a	Maximum allowable acceleration		50	m/s ²

Thermal Characteristics

Symbol	Item	Conditions	Values	Units
R _{th(j-c)}	Thermal Impedance, max.	Junction to Case	0.65	°C/W
R _{th(c-s)}	Thermal Impedance, max.	Case to Heatsink	0.20	°C/W

Electrical Characteristics

Symbol	Item	Conditions	Values			Units
			Min.	Typ.	Max.	
V _{TM}	Peak On-State Voltage, max.	T=25°C I _T =200A			1.95	V
I _{RRM} /I _{DRM}	Repetitive Peak Reverse Current, max. / Repetitive Peak Off-State Current, max.	T _{VJ} =T _{VJM} , V _R =V _{RRM} , V _D =V _{DRM}			15	mA
V _{TO}	On state threshold voltage	For power-loss calculations only (T _{VJ} =125°C)			1.0	V
r _T	Value of on-state slope resistance, max	T _{VJ} =T _{VJM}			4.5	mΩ
V _{GT}	Gate Trigger Voltage, max.	T _{VJ} =25°C, V _D =6V			2.5	V
I _{GT}	Gate Trigger Current, max.	T _{VJ} =25°C, V _D =6V			150	mA
V _{GD}	Non-triggering gate voltage, max.	T _{VJ} =125°C, V _D =2/3V _{DRM}			0.25	V
I _{GD}	Non-triggering gate current, max.	T _{VJ} =125°C, V _D =2/3V _{DRM}			6	mA
I _L	Latching current, max.	T _{VJ} =25°C, R _G =33Ω		300	600	mA
I _H	Holding current, max.	T _{VJ} =25°C, V _D =6V		150	250	mA
tgd	Gate controlled delay time	T _{VJ} =25°C, I _G =1A, dI _G /dt=1A/us		1		us
tq	Circuit commutated turn-off time	T _{VJ} =T _{VJM}		80		us

Performance Curves**Fig1. Power dissipation****Fig2. Forward Current Derating Curve****Fig3. Transient thermal impedance****Fig4. Max Non-Repetitive Forward Surge Current****Fig5. Forward Characteristics**

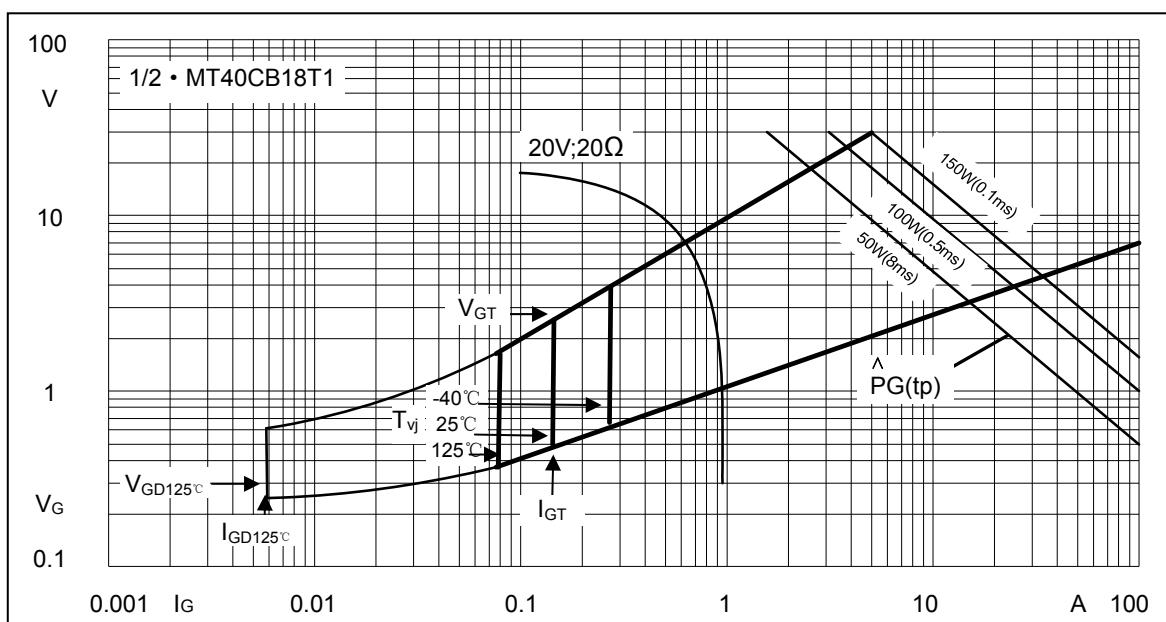
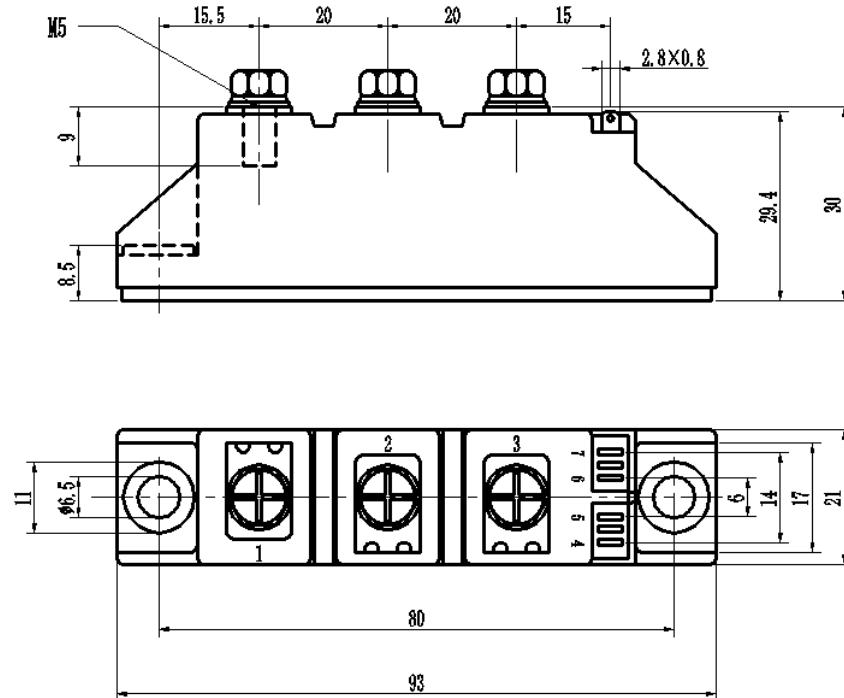


Fig6. Gate trigger Characteristics

Package Outline Information

CASE: T1



Dimensions in mm